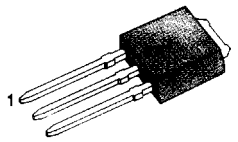
SGU6N60UF

N-CHANNEL IGBT

FEATURES

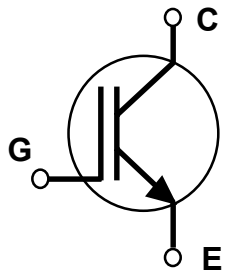
* High Speed Switching
* Low Saturation Voltage
  : V_{CE}(sat) = 2.1 V (@ Ic=3A)
* High Input Impedance

I - PAK



APPLICATIONS

* AC & DC Motor controls
* General Purpose Inverters
* Robotics , Servo Controls
* Power Supply
* Lamp Ballast



ABSOLUTE MAXIMUM RATINGS

Symbol	Characteristics	Rating	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Collector Current @ Tc = 25℃	6	A
	Collector Current @ Tc = 100℃	3	A
$I_{CM\ (1)}$	Pulsed Collector Current	25	A
P_C	Maximum Power Dissipation @Tc = 25℃	30	W
	Maximum Power Dissipation @Tc = 100℃	12	W
Tj	Operating Junction Temperature	-55 ~ 150	℃
Tstg	Storage Temperature Range	-55 ~ 150	℃
T_L	Maximum Lead Temp. For Soldering Purposes, 1/8″ from case for 5 seconds	300	℃

Notes: (1) Repetitive rating : Pulse width limited by max. junction temperature

ELECTRICAL CHARACTERISTICS
(T_C=25℃,Unless Otherwise Specified)

Symbol	Characteristics	Test Conditions	Min	Typ	Max	Units
BV_{CES}	C - E Breakdown Voltage	V_{GE} = 0V , I_C = 250㎂	600	-	-	V
$\Delta V_{CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	V_{GE} = 0V , I_C = 1mA	-	0.6	-	V/℃
$V_{GE(th)}$	G - E threshold voltage	I_C = 3mA , V_{CE} = V_{GE}	4.0	5.5	7.5	V
I_{CES}	Collector cutoff Current	V_{CE} = V_{CES} , V_{GE} = 0V	-	-	250	uA
I_{GES}	G - E leakage Current	V_{GE} = V_{GES} , V_{CE} = 0V	-	-	100	nA
V_{CE}(sat)	Collector to Emitter saturation voltage	Ic=3A, V_{GE} = 15V	-	2.1	2.6	V
		Ic=6A, V_{GE} = 15V	-	2.6	-	V
Cies	Input capacitance	V_{GE} = 0V , f = 1㎒	-	220	-	pF
Coes	Output capacitance	V_{CE} = 30V	-	22	-	pF
Cres	Reverse transfer capacitance		-	7	-	pF
td(on)	Turn on delay time	V_{CC} = 300V , I_C = 3A	-	15	-	ns
tr	Turn on rise time	V_{GE} = 15V	-	22	-	ns
td(off)	Turn off delay time	R_G = 80 Ω	-	40	70	ns
tf	Turn off fall time	Inductive Load	-	80	160	ns
Eon	Turn on Switching Loss		-	75	-	uJ
Eoff	Turn off Switching Loss		-	30	-	uJ
Ets	Total Switching Loss		-	100	125	uJ
Qg	Total Gate Charge	Vcc = 300V	-	15	22	nC
Qge	Gate-Emitter Charge	V_{GE} = 15V	-	5	8	nC
Qgc	Gate-Collector Charge	Ic = 3A	-	4	6	nC
Le	Internal Emitter Inductance	Measured 5mm from PKG	-	7.5	-	nH

THERMAL RESISTANCE

Symbol	Characteristics	Min	Typ	Max	Units
$R_{\theta}JC$	Junction-to-Case	-	-	4.0	℃/W
$R_{\theta}JA$	Junction-to-Case	-	-	110	℃/W
$R_{\theta}CS$	Case-to-Sink	-	1.7	-	℃/W

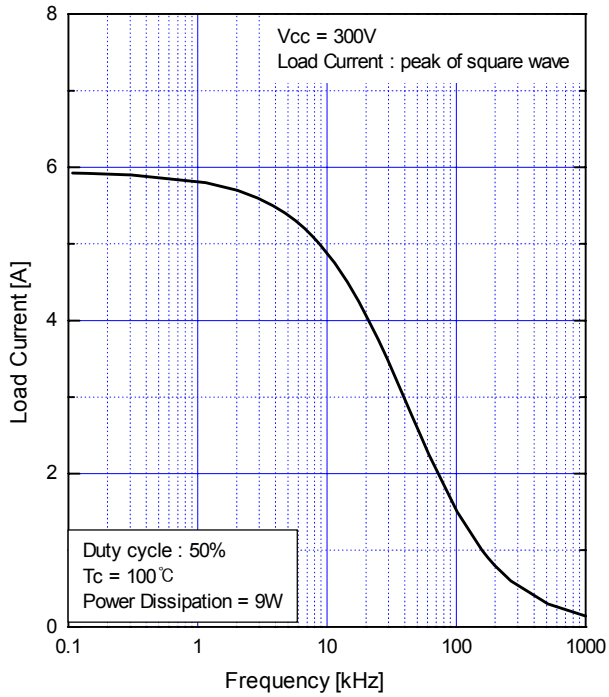


Fig.1 Typical Load Current vs. Frequency

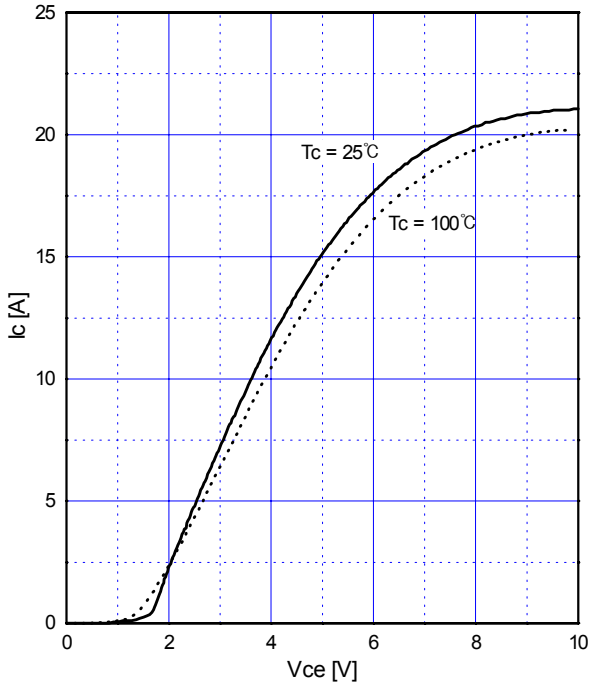


Fig.2 Typical Output Characteristics

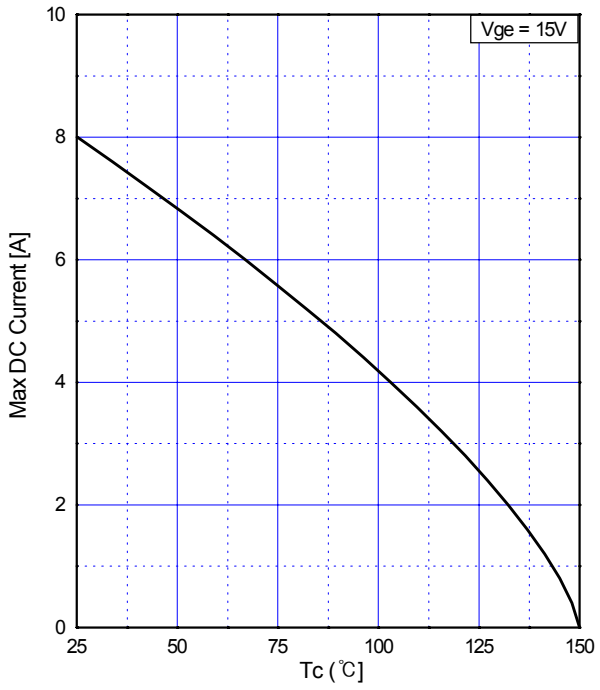


Fig.3 Maximum Collector Current vs. Case Temperature

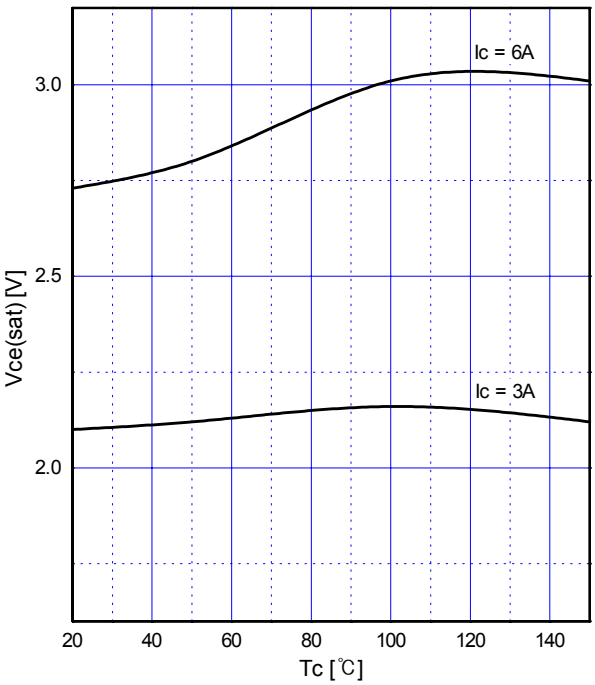


Fig.4 Collector to Emitter Voltage vs. Case Temperature

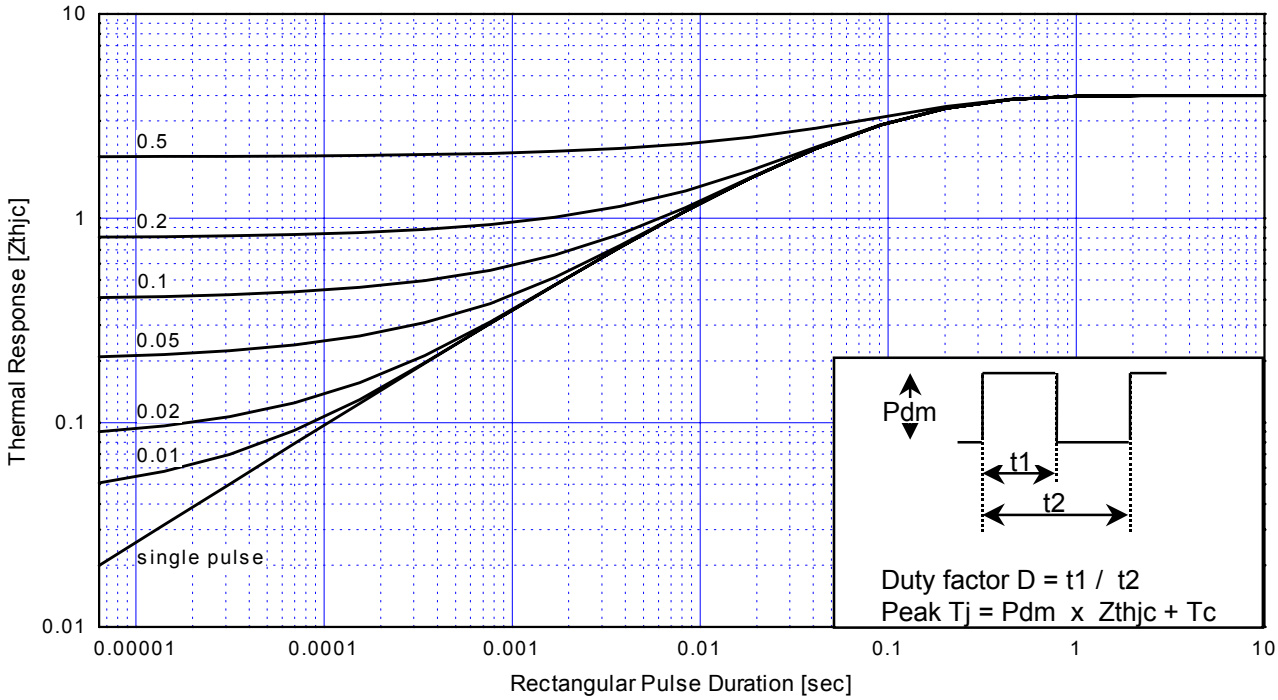


Fig.5 Maximum Effective Transient Thermal Impedance, Junction to Case

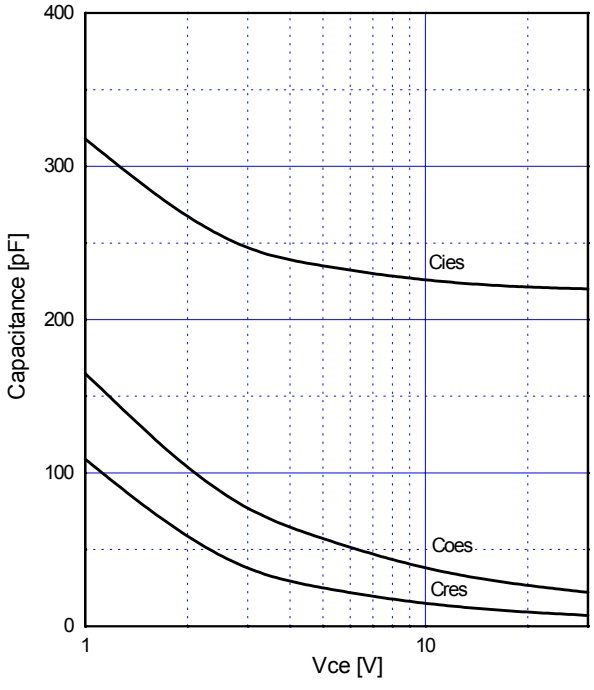


Fig.6 Typical Capacitance vs.
Collector to Emitter Voltage

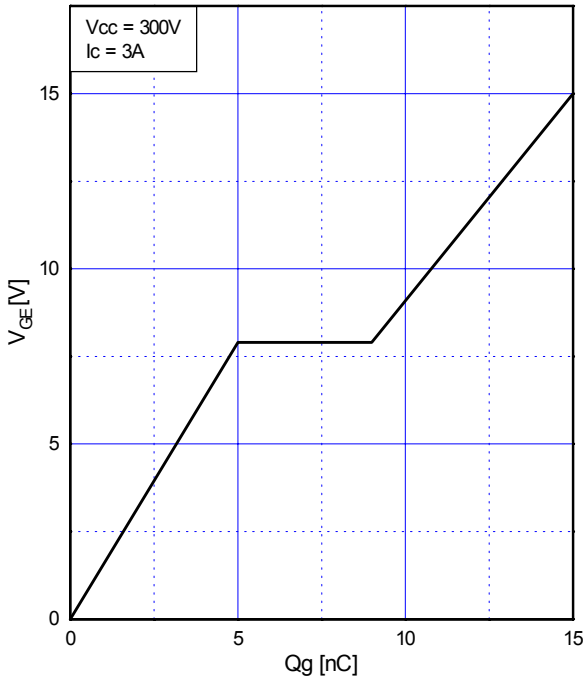


Fig.7 Typical Gate Charge vs.
Gate to Emitter Voltage

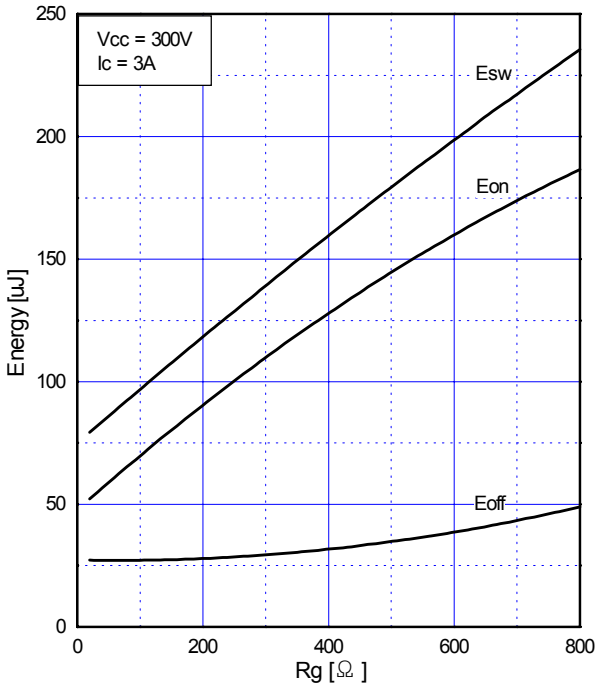


Fig.8 Typical Switching Loss vs. Gate Resistance

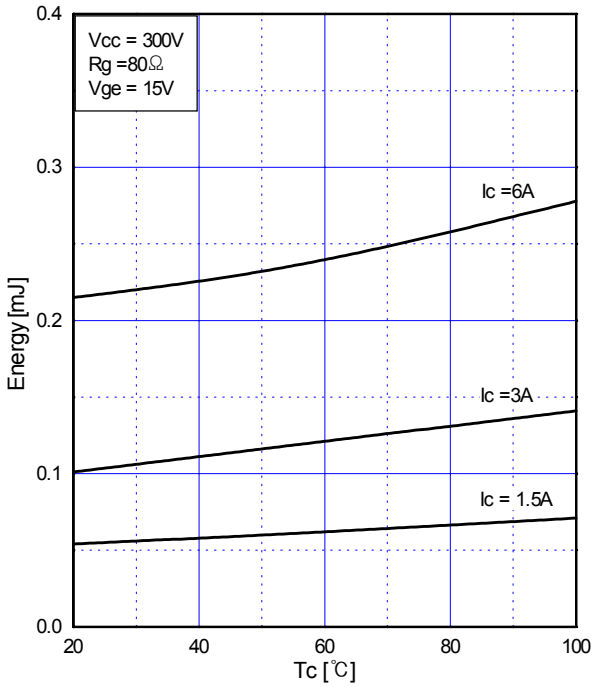


Fig.9 Typical Switching Loss vs. Case Temperature

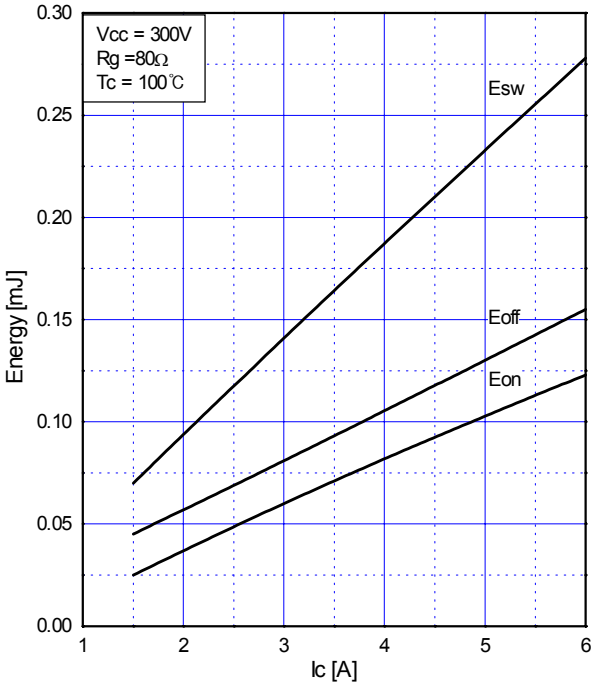


Fig.10 Typical Switching loss vs. Collector to Emitter Current

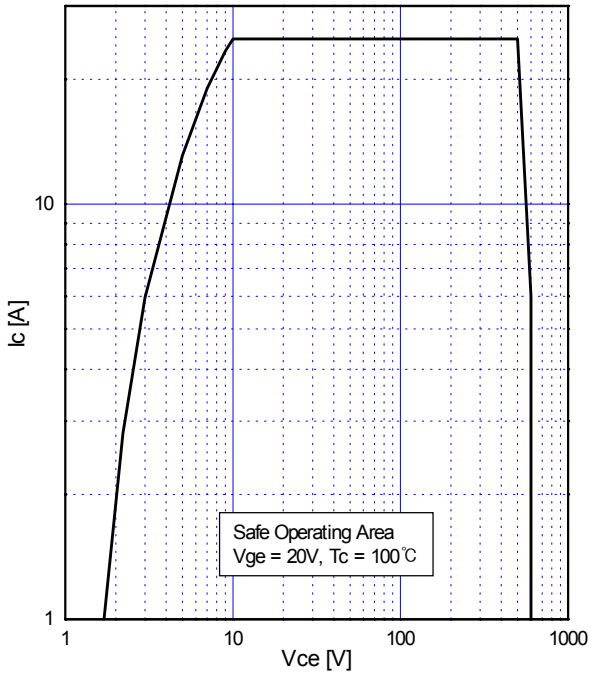


Fig.11 Turn-off SOA